



Molded Package Type IGBTs

Molded package types, such as microwave ovens / Horizontal deflection circuit

Device type	V _{CES}	V _{GES}	I _C	P _C	V _{CE(sat)} (V _{GE} =15V)		t _f	R _{th(j-c)}	Package	Net mass Grams
	Volts	Volts	Cont. Amps.	Watts	Max. Volts	I _C Amps.				
1MBH60D-090A	900	±20	60	260	3.2	60	0.8	0.481	TO-3PL	9.5
1MBH65D-090A	900	±20	65	300	5.54	60	0.77	0.417	TO-3PL	9.5

Fast Recovery Diodes for IGBT

Molded FRD

Device type	V _{RRM}	I _{FM}	V _F	trr	Package	Net mass
	Volts	Amps.	Volts	Switching time (Max.) (μsec.) di/dt=100A/μs 70% recovery		Grams
ERW01-060	600	5(T _C =118°C)	3 (I _F = 5A)	0.3 (I _F = 5A, V _R =200V)	TO-220AB(single)	2.3
ERW02-060	600	10(T _C =100°C)	3 (I _F =10A)	0.3 (I _F =10A, V _R =200V)	TO-220AB(single)	2.3
ERW03-060	600	15(T _C =92°C)	3 (I _F =15A)	0.3 (I _F =15A, V _R =200V)	TO-220AB(single)	2.3
ERW04-060	600	20(T _C =91°C)	3 (I _F =20A)	0.3 (I _F =20A, V _R =200V)	TO-220AB(single)	2.3
ERW05-060	600	30(T _C =81°C)	3 (I _F =30A)	0.3 (I _F =30A, V _R =200V)	TO-220AB(single)	2.3
ERW06-060	600	50(T _C =77°C)	3 (I _F =50A)	0.3 (I _F =50A, V _R =200V)	TO-3P(single)	5.5
ERW07-120	1200	2.5(T _C =129°C)	3 (I _F = 2.5A)	0.35 (I _F = 2.5A, V _R =200V)	TO-220AB(single)	2.3
ERW08-120	1200	5(T _C =127°C)	3 (I _F = 5A)	0.35 (I _F = 5A, V _R =200V)	TO-220AB(single)	2.3
ERW09-120	1200	8(T _C =124°C)	3 (I _F = 8A)	0.35 (I _F = 8A, V _R =200V)	TO-220AB(single)	2.3
ERW10-120	1200	10(T _C =123°C)	3 (I _F =10A)	0.35 (I _F =10A, V _R =200V)	TO-220AB(single)	2.3
ERW11-120	1200	15(T _C =122°C)	3 (I _F =15A)	0.35 (I _F =15A, V _R =200V)	TO-3P(single)	5.5
ERW12-120	1200	25(T _C =113°C)	3 (I _F =25A)	0.35 (I _F =25A, V _R =200V)	TO-3P(single)	5.5
ERW13-060	600	50(T _C =90°C)	3 (I _F =50A)	0.3 (I _F =50A, V _R =200V)	TO-3PL	9.5